

EECE 511 - Lecture 4

Note Title

1/22/2015

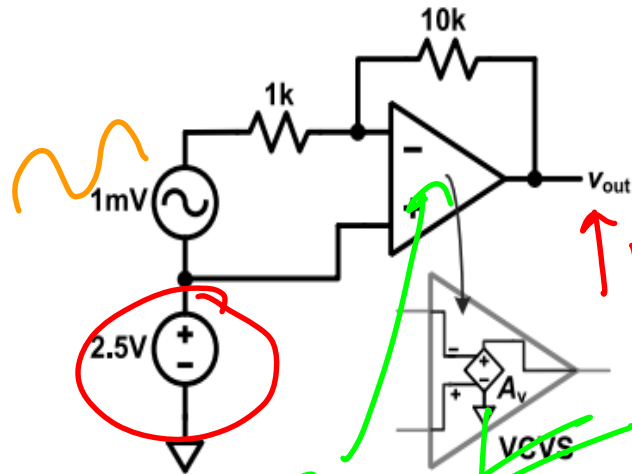


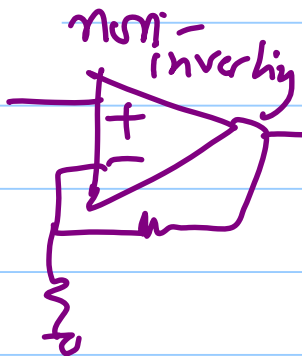
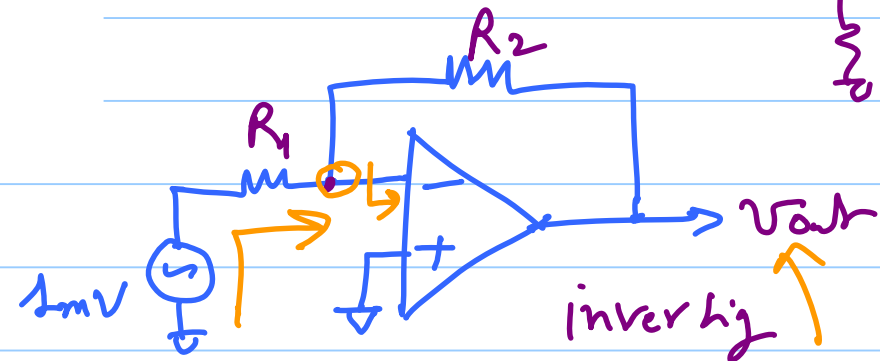
Figure 1

↑ well-defined
DC level

10^6

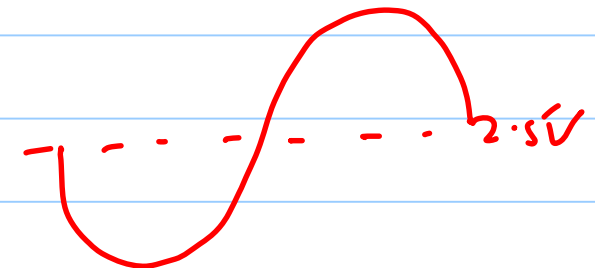
1. Calculate the DC and AC voltages in the circuit nodes. What is the AC gain of the amplifier?
2. What are the DC and AC currents (magnitude and direction) flowing across the resistors?

AC picture



KCL:

$$\frac{V_{in}}{R_1} + \frac{V_{out}}{R_2} = 0$$



* r_o change with "L" & " V_{ov} "

$$I_{D,sat} = \frac{Kp_n}{2} \frac{W}{L} V_{ov}^2$$

$$\lambda \propto \frac{1}{L}$$

$$r_o = \frac{1}{\lambda I_{D,sat}} \propto \frac{L^2}{V_{ov}^2}$$

Long-channel
MOSFET

* for a fixed $V_{GS} \Rightarrow$ fixed V_{ov} , $r_o \uparrow$ if $L \uparrow$ *

* for fixed L , $V_{ov} \downarrow \Rightarrow I_D \downarrow$, $r_o \uparrow$ *

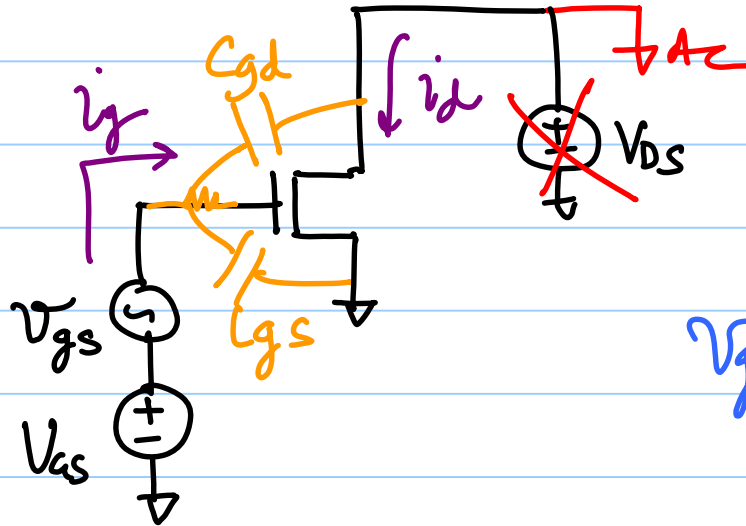
$$g_{ain} \triangleq g_m r_o = \frac{\cancel{\beta} V_{ov}}{\lambda \cdot \cancel{\beta} V_{ov}^2} \propto \frac{L}{V_{ov}}$$

$$g_{ain} \Rightarrow g_m r_o \propto \frac{L}{V_{ov}}$$

MOSFET Transition Frequency (f_T):

f_{max}
RF IC

AC picture



@ $f = f_T$

$$\left| \frac{i_d}{i_g} \right| = 1 \quad \text{or } 0 \text{ dB}$$

$$v_{gs} = \frac{i_g}{s(C_{gd} + C_{gs})} \rightarrow \textcircled{1}$$

$$i_d = g_m v_{gs} \rightarrow \textcircled{2}$$

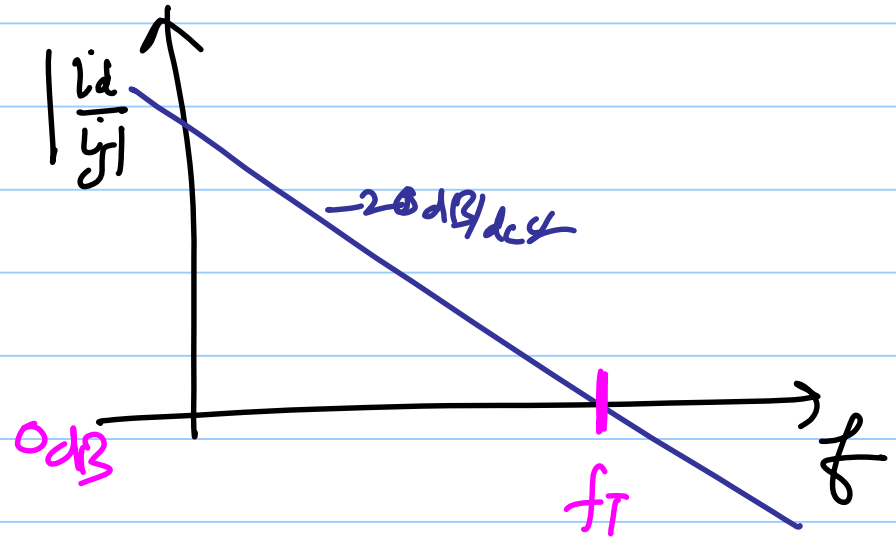
$$i_d = \frac{g_m i_g}{s(C_{gd} + C_{gs})}$$

$$\Rightarrow \frac{i_d}{i_g} = \frac{g_m}{(C_{gd} + C_{gs})s}$$

$$\left| \frac{i_d}{i_g}(f) \right| = \frac{g_m}{2\pi f (C_{gd} + C_{gs})} \quad \stackrel{\Delta}{=} 1$$

$$f_T = \frac{g_m}{2\pi (C_{gs} + C_{gd})}$$

in sat
 $C_{gs} \gg C_{gd}$



$$f_T \approx \frac{g_m}{2\pi C_{gs}}$$

$g_m \propto V_{ov}$

$\left\{ \frac{W}{L} \right\}$
 $\{V_{ov}\}$

C_{gs} with WL

f_T ignores the junction caps and is defined such that ϕ_0 is excluded.

$$f_T = \frac{g_m}{2\pi C_{gs}} = \frac{\frac{\mu_n}{2\pi} \frac{W}{L} \frac{V_{ov}}{V_{ov}}}{\frac{2}{3} C_{ox}' WL}$$

$$\approx \frac{3\mu_n}{4\pi} \cdot \frac{V_{ov}}{L^2}$$

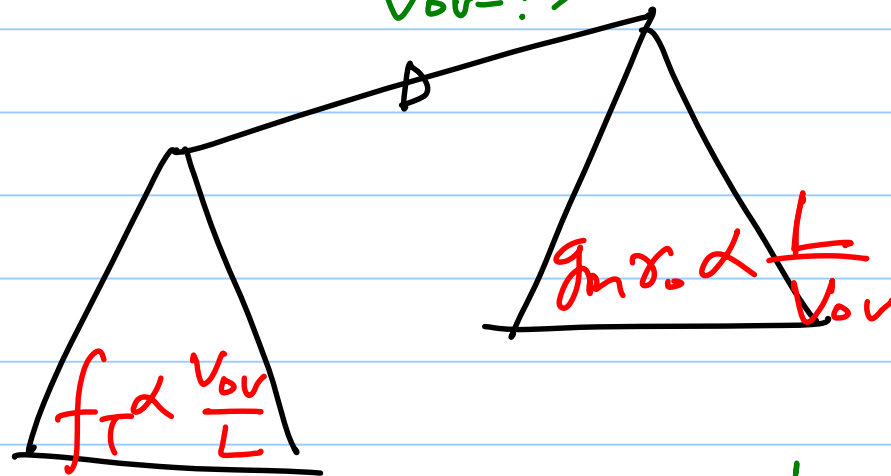
$$f_T \propto \frac{V_{ov}}{L^2}$$

long-L
mosfets

for short-channel

$$f_T \propto \frac{V_{ov}}{L}$$

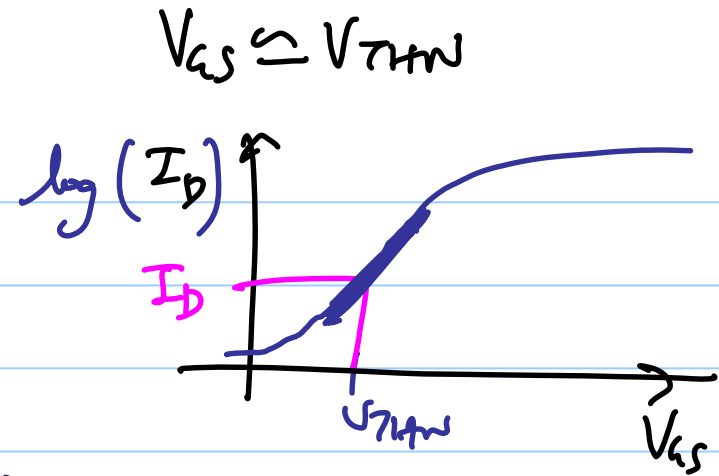
$L=?$
 $V_{ov}=?$ } Technology



for first design $L = L_{min}$
 moderate/slow speed $V_{ov} \leq 3-5\% V_{DD}$
 $V_{ov} 1-2\% V_{DD}$
 $3-5 L_{min}$

subthreshold

$$i_D = I_{D0} \cdot \frac{W}{L} e^{\frac{V_{GS} - V_{THW}}{nV_T}} \quad V_T = \frac{kT}{q}$$



$$g_m = \left. \frac{\partial i_D}{\partial V_{GS}} \right|_{V_{GS} = V_{THW}} = \left(I_{D0} \frac{W}{L} e^{\frac{V_{GS} - V_{THW}}{nV_T}} \right) \cdot \frac{1}{nV_T}$$

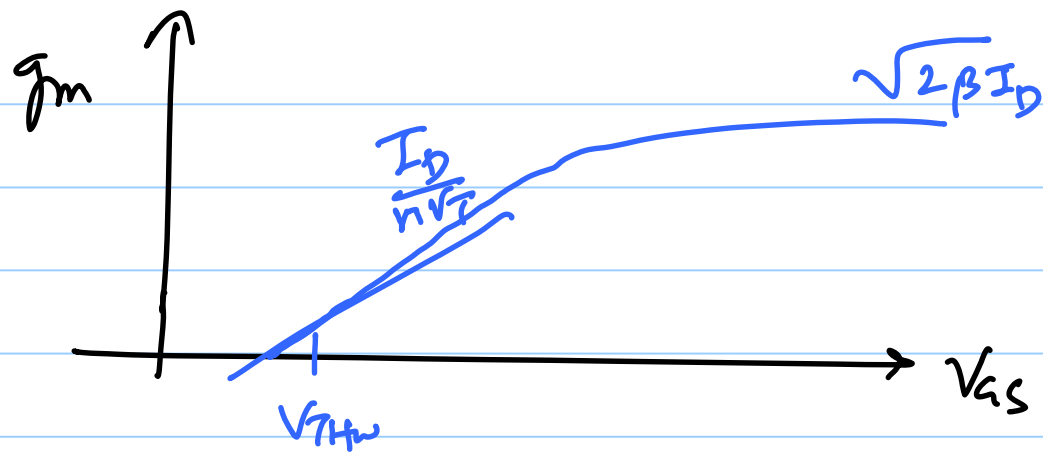
$$g_m = \frac{I_D}{nV_T}$$

$g_m \propto I_D \rightarrow \text{sub } V_T$
 $g_m \propto \sqrt{I_D}$ inversion

$\frac{g_m}{I_D}$ ratio

$$V_{OV} \propto \frac{1}{\sqrt{WL}}$$

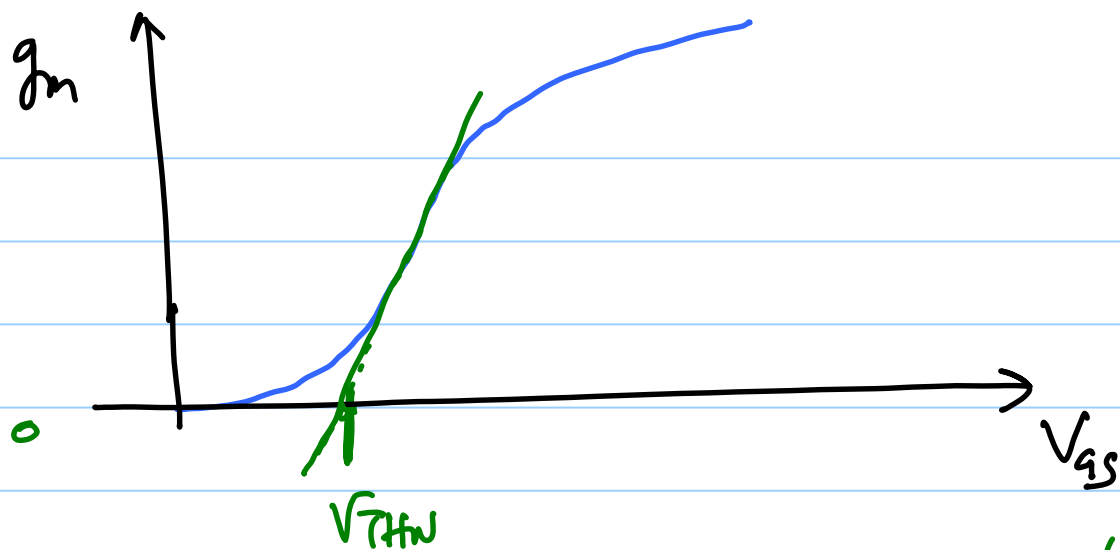
$V_{OV} \Rightarrow I_{mV}$
 $\hookrightarrow V_{GS} - V_{THW}$
 variations due process



$$\left(\frac{g_m}{I_D} \right)$$

low- f_T in
sub V_T .

In sub $V_T \Rightarrow$ NMOS look like BJT.



$$g_m = \beta_m (V_{gs} - V_{thw})$$

$g_m \neq 0$ when $V_{gs} = V_{thw}$

$$I_D = \frac{k\mu_n}{2} \cdot \frac{W}{L} (\mu_{n, Cox'}) (V_{GS} - V_{THW})^2$$

$$\frac{\partial I_D}{\partial T}$$

T ↑

$$\mu_n(T) = \mu_n(T_0) \left(\frac{T}{T_0} \right)^{-3/2}$$

$$V_{THW} = -V_{ms} - 2V_{fp} + \frac{Q_{bo}' - Q_{ss}'}{C_{ox}'}$$

$$\frac{\partial V_{THW}}{\partial T} \approx -\frac{k}{q} \ln \left(\frac{N_D, poly}{N_A} \right)$$

$$\approx -1 \text{ mV}/^\circ\text{C}$$

$V_{THN} \downarrow \Rightarrow I_D \uparrow \leftarrow$ dominates for $V_{GS} \lesssim V_{THN}$
 $\mu_{mn} \downarrow \Rightarrow I_D \downarrow \leftarrow$ dominates at large currents

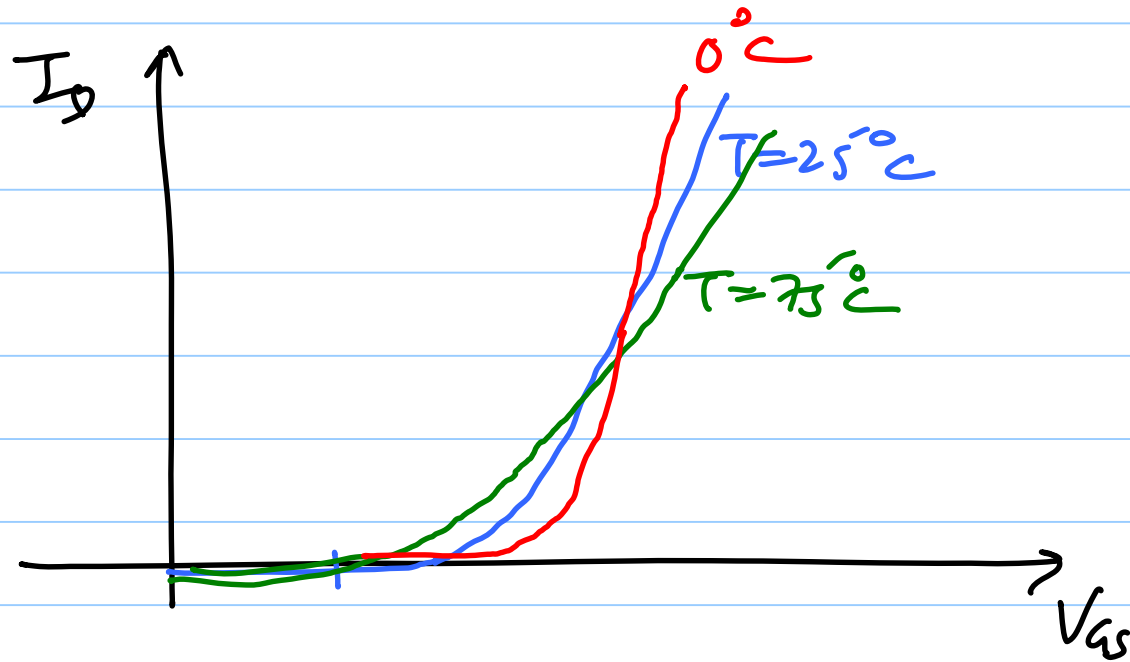


Figure-of-merit :

$$GFT \Rightarrow (g_m r_o) \cdot f_T$$

Long-channel process:

$$g_m r_o f_T = \frac{g_m^2}{2\pi C_{gs}} \cdot \frac{1}{\lambda I_D} = \frac{3\mu_n}{2\pi L^2} \propto \frac{\mu_n}{L}$$

$g_m r_o f_T$ is constant for a device with
with fixed L
independent of the current level

"L"

$$(g_m r_o) (f_T)$$

$\uparrow V_{ov} \Rightarrow I_D$